



**MODELLING AND OPTIMIZATION OF NANO  
POWDER MIXED MICRO WEDM PROCESS USING  
ARTIFICIAL NEURAL NETWORKS AND GENETIC  
ALGORITHM**

**BY**

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## ABSTRACT

Micro Wire Electro Discharge Machining ( $\mu$ -WEDM) is a non-conventional machining process which is used for machining complex structural design and achieving net-shape machining. This machining method is mainly used for conductive materials. However, semiconductor materials like Silicon (Si) can not be effectively machined due to its high resistivity. For this requires some advanced technique to enhance the machining process and efficiency. One technique could be the conductive coating on the workpiece material and use of nano powder mixed dielectric fluid. So far not much research has been conducted to machine Si like materials by using nano powder mixed dielectric fluid. Moreover, there is no intelligent system available that can help the users to select optimal parameters to achieve specific machining goal. One aim at this study is to carry out nano powder assisted micro WEDM for temporarily coated Silicon samples to achieve improved surface finish with more machining efficiency. For this purpose, three different type of nano powders like Aluminium(Al), Silicon (Si) and Graphite (C) were used for machining highly doped Silicon workpiece material to observe the effect of nano powders on the machining process. Before machining the workpiece material (Si) was coated temporarily by a highly conductive material like gold (Au) metal to make the workpiece more conductive during the machining process. The research showed that by using nano powder mixed  $\mu$ -WEDM process, Material Removal Rate (MRR) was improved by almost ~48% than traditional machining process. However, Spark Gap (SG) was also increased by ~28% for nano powder assisted WEDM as compared to dielectric EDM oil used machining. Further, Al powder mixed WEDM process have resulted higher MRR but less SG than any other powder. It was found that at specific condition (at 80V, 13 pF, 0.2g/L powder concentration, 320 nm gold thickness) the Al nano powder mixed dielectric used machining can produce the lowest surface roughness as 26 nm. It was also observed that at lower powder concentration and specific parametric conditions C, Al can easily produce nano range surface roughness where Si powder produces comparatively worse surface roughness than other powders. Therefore, it can be concluded that average surface roughness (ASR) can be improved by maximum ~65% for nano powder assisted machining as compared to conventional WEDM. Another main purpose of this research is to establish an intelligent system that can suggest suitable parameters for nano powder assisted  $\mu$ -WEDM operation (for Si machining) to achieve certain machining goal. The experimental datasets of this study are used carefully to create a successful predictive model using artificial neural network (ANN). On the basis of the established predictive model, some experiments have been further conducted to assess the validity of the model. Then ANN model has been further optimized by using genetic algorithm (GA) to get required input for optimum output results. Finally, the accuracy of the modelling has been calculated by measuring the error percentage which is less than 5-10% for the model. This infers the modelling efficiency up to 90%.

## خلاصة البحث

التصنيع الآلي بالتفريغ الكهربائي وباستخدام السلك الميكروي ( $\mu$ -WEDM) هو عملية غير تقليدية للتصنيع الآلي والتي تستخدم تصنيحاً ذو تصميم هيكلية معقد لتحقيق تصنيع آلي صافي الشكل. تستخدم هذه الطريقة بشكل أساسي للتصنيع الآلي في المواد الناقلة. ومع ذلك فإن المواد النصف ناقلة كالسيليكون لا يمكن تصنيعها آلياً بشكل فعال بسبب مقاومتها العالية. لذلك فهي تحتاج بعض التقنيات المتطورة لتحسين عملية التصنيع الآلي وتحسين الفعالية. إحدى هذه التقنيات هي تأمين غطاء ناقل لمادة القطع المشغولة واستخدام سائل عازل ممزوج مع المسحوق النانوي. وحتى الآن لم يتم إجراء الكثير من البحوث لتصنيع المواد المشابهة للسيليكون (Si) باستخدام السائل العازل الممزوج مع المسحوق النانوي، وفوق ذلك، لا يتوفر نظام ذكي يستطيع مساعدة المستخدمين لتحديد العوامل المتغيرة المثالية لتحقيق الهدف المخصص للتصنيع. أحد الأهداف الأساسية لهذه الدراسة هو إجراء التصنيع الآلي بالتفريغ الكهربائي وباستخدام السلك الميكروي وبمساعدة المسحوق النانوي على عينات السيليكون المطلي بشكل مؤقت لتحسين صقل الأسطح مع زيادة الفعالية. ولتحقيق هذا الغرض، تم استخدام ثلاثة أنواع مختلفة من المساحيق النانوية كالألمنيوم (Al)، والسيليكون (Si) والجرافيت (C) لتصنيع مواد القطع المشغولة والمعالجة بشكل كبير بمادة السيليكون ولمراقبة تأثير تلك المساحيق النانوية على عملية التصنيع. تم تغليف مادة القطع (السيليكون) قبل التصنيع مؤقتاً بمادة عالية الناقلة كمعدن الذهب (Au) لجعل القطع أكثر ناقلية خلال عملية التصنيع. يعرض هذا البحث ذلك باستخدام التصنيع الآلي بالتفريغ الكهربائي وباستخدام السلك الميكروي وبمزج المسحوق النانوي. تم تحسين معدل إزالة المادة MRR بمقدار تقريبي 48% مقارنة بطرق التصنيع التقليدية، ومع ذلك فإن Spark Gap (SG) زادت بحوالي 28% بوجود المسحوق النانوي بالمقارنة مع وجود الزيت العازل. بالإضافة إلى ذلك، عملية مزج مسحوق الألمنيوم في التصنيع الآلي بالتفريغ الكهربائي وباستخدام السلك أدت إلى زيادة الـ MRR ونقصان الـ SG بالمقارنة مع المساحيق الأخرى. كما تم إثبات أن العازل الممزوج بمسحوق الألمنيوم النانوي في عملية التصنيع وفي شروط خاصة (80V، 13 pF)، تركيز المسحوق 0.2g/L، سماكة الذهب (320 nm) يؤدي إلى انقاص خشونة السطح لـ 26 nm. كما وجد أن المسحوق ذو التركيز الأقل وذو الشروط الخاصة لقيم العوامل المتغيرة كالجرافيت والألمنيوم يمكن أن ينتج بسهولة معدل خشونة سطح بمجال نانوي. في حين أن مسحوق الـ Si ينتج معدل خشونة سطح أسوأ مقارنة بالمساحيق الأخرى. وفي الخلاصة يمكن إستنتاج أن متوسط خشونة السطح يمكن تحسينها بحد أقصى يصل إلى 65% تقريباً باستخدام المسحوق النانوي المساعد في عملية التصنيع مقارنة بالطرق التقليدية. والهدف الرئيسي الآخر من هذا البحث هو انشاء نظام ذكي يستطيع اقتراح عوامل متغيرة لعملية  $\mu$ -WEDM المدعومة بالمسحوق النانوي (التصنيع الآلي للسيليكون) من أجل تحقيق الهدف المحدد للتصنيع. تم استخدام بيانات التجارب في هذه الدراسة بدقة لإيجاد نموذج تنبؤي ناجح باستخدام الشبكة العصبية الاصطناعية (ANN). بالاعتماد على هذا النموذج التنبؤي المنشأ، أجريت بعض التجارب الإضافية لتقييم صلاحية هذا النموذج. بعد ذلك تمّت أمثلة نموذج الشبكة العصبية الاصطناعية باستخدام الخوارزمية الجينية (GA) لتأمين المدخلات المطلوبة للحصول على نتائج مخرجات مثالية. وفي النهاية، تم حساب دقة النمذجة عن طريق قياس نسبة الخطأ والتي كانت أقل من (5-10)% للنموذج. وهذا يدل على أن كفاءة النموذج يمكن أن تصل إلى 90%.

# APPROVAL PAGE

I certify that I have supervised and read this study and that in my opinion, it conforms to acceptable standards of scholarly presentation and is fully adequate, in scope and quality, as a thesis for the degree of Master of Science (Mechatronics Engineering).

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## DECLARATION

I hereby declare that this dissertation is the result of my own investigations, except where otherwise stated. I also declare that it has not been previously or concurrently Submitted as a whole for any other degrees at IIUM or other institutions.

Sams Jarin

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# TABLE OF CONTENTS

Abstract .....	ii
Abstract in Arabic .....	iii
Approval page .....	iv
Declaration page .....	v
Copyright page .....	vi
Acknowledgements .....	vii
List of tables .....	xi
List of figures .....	xiii
List of symbols .....	xix
List of abbreviations .....	xxi
<b>CHAPTER ONE: INTRODUCTION .....</b>	<b>1</b>
1.1 Background .....	1
1.2 Problem statement and its significance .....	3
1.3 Research objectives .....	4
1.4 Research methodology .....	4
1.5 Research scope .....	9
1.6 Thesis organization .....	9
<b>CHAPTER TWO: LITERATURE REVIEW .....</b>	<b>11</b>
2.1 Introduction .....	11
2.2 Electric discharge machining of Silicon .....	12
2.3 Application of Conductive coating in EDM .....	19
2.4 Powder mixed electric discharge machining .....	22
2.5 Application of ANN and GA for EDM/WEDM .....	30
2.4 Summary .....	35
<b>CHAPTER THREE: RESEARCH METHODOLOGY .....</b>	<b>36</b>
3.1 Introduction .....	36
3.2 Experimentation and characterization .....	36
3.2.1 Machining process parameters and their levels .....	37
3.2.2 Preparation of Si wafer .....	39
3.2.3 Gold coating process of Si wafer .....	41
3.2.4 Experimental set-up for WEDM process .....	43
3.2.5 Post machining cleaning process of the sample .....	46
3.2.5.1 Wet etching process of machined Si for EDXing .....	48
3.2.6 Characterization steps .....	50
3.2.6.1 Field emission scanning electron microscopy analysis .....	50
3.2.6.2 Alicona infinite focus machine .....	51
3.2.6.3 Olympus infinite focus machine .....	52
3.2.6.4 Energy dispersive x-ray Spectroscopy analysis .....	54
3.2.7 Machining stability testing .....	55
3.3 Model development and optimization techniques .....	56
3.3.1 Artificial Neural Network (ANN) model development .....	57



3.3.2 Model parameters selection process.....	58
3.3.3 Neural architecture .....	58
3.3.4 Collection of Data (machining parameters) for modelling .....	59
3.3.5 Model performance evaluation and validation process.....	60
3.3.6 Genetic Algorithm for optimizing the ANN model .....	61
3.4 Summary.....	62
<b>CHAPTER FOUR: RESULTS AND DISCUSSIONS.....</b>	<b>63</b>
4.1 Introduction.....	63
4.2 Experimental investigation and characterization.....	64
4.2.1 Influence of Nano powders on $\mu$ -WEDM of gold coated Si.....	64
4.2.1.1 Study of Material removal rate.....	64
4.2.1.2 Study of spark gap .....	67
4.2.1.3 Study of average surface roughness .....	69
4.2.1.4 Study of unevenness factor and machining stability .....	74
4.2.2 Influence of discharge energies on $\mu$ -WEDM of gold coated Si ....	77
4.2.2.1 Study of Material removal rate.....	78
4.2.2.2 Study of Spark gap .....	82
4.2.2.3 Study of Average surface roughness .....	86
4.2.2.4 Study of unevenness factor and machining stability .....	90
4.3 Summary.....	93
<b>CHAPTER FIVE: EXPERIMENTAL MODELING AND OPTIMIZATION ..</b>	<b>94</b>
5.1 Introduction.....	94
5.2 Development and Evaluation of the ANN-GA model.....	95
5.2.1 Parameters settings.....	96
5.2.2 Neural architecture of MLP .....	97
5.2.2.1 Learning Algorithm of the model.....	97
5.2.2.2 Number of hidden layers and nodes .....	98
5.2.2.3 Strategy of parameters selection for the model .....	99
5.2.2.4 Levenberg-Marquardt Training Algorithm .....	100
5.2.3 Performance Evaluation techniques of the ANN modeling .....	103
5.2.4 ANN model performances for C, Al and Si NPM $\mu$ -WEDM .....	103
5.2.4.1 ANN modeling for SG response.....	104
5.2.4.2 ANN modeling validation process for SG response.....	109
5.2.4.3 ANN modeling for MRR response.....	112
5.2.4.4 ANN modeling validation process for MRR response.....	114
5.2.4.5 ANN-GA modeling for ASR response.....	117
5.2.4.6 ANN modeling validation process for ASR response.....	120
5.2.5 Optimization by Genetic Algorithm.....	122
5.2.6 Structure of Genetic Algorithm.....	122
5.2.6.1 Fitness Function.....	124
5.2.6.2 Parameter selection for GA .....	125
5.2.7 Implementation of GA Optimization for NPM $\mu$ -WEDM.....	127
5.2.7.1 GA optimization for the SG .....	127
5.2.7.2 GA optimization for the MRR.....	129
5.2.7.3 GA optimization for the ASR.....	130
5.3 Summary.....	131

<b>CHAPTER SIX: CONCLUSION AND RECOMMENDATION.....</b>	<b>133</b>
6.1 Conclusion .....	133
6.2 Recommendation .....	136
<b>REFERENCES.....</b>	<b>138</b>
<b>PUBLICATIONS .....</b>	<b>145</b>
<b>APPENDIX A: CNC G-CODING AND MATLAB CODING .....</b>	<b>146</b>
<b>APPENDIX B: TABLES OF MACHINING RESULTS.....</b>	<b>157</b>
<b>APPENDIX C: FIGURES.....</b>	<b>163</b>
<b>APPENDIX D: OTHERS .....</b>	<b>170</b>

## LIST OF TABLES

3.1	Definition of Input and Output parameters	37
3.2	Properties of the Si Workpiece materials.	38
3.3	Process Parameters and their levels	39
3.4	Properties of Aluminum, Silicon and Graphite Nano Powder.	40
5.1	The used Different number of hidden nodes for the first layer of the model.	99
5.2	The different ratio of the used dataset to test for a particular model.	100
5.3	The effect of different number of hidden neurons on the network model.	106
5.4	Validation testing of the ANN model for SG output of C nano powder.	109
5.5	Validation testing of the ANN model for MRR output of Al nano powder.	115
5.6	Validation testing of the ANN model for ASR output of Al nano powder.	120
5.7	Optimum process parameters (De-normalized values) for SG.	129
5.8	Optimum process parameters (De-normalized values) for MRR.	130
5.9	Optimum process parameters (De-normalized values) for ASR.	131
B.1	$\mu$ -WEDM Results For 0.2g C suspended dielectric used machining	157
B.2	$\mu$ -WEDM Results For 0.2g Al suspended dielectric used machining	157
B.3	$\mu$ -WEDM Results For 0.2g Si suspended dielectric used machining	158
B.4	$\mu$ -WEDM Results For 1.0g C suspended dielectric used machining	158
B.5	$\mu$ -WEDM Results For 1.0g Al suspended dielectric used machining	159
B.6	$\mu$ -WEDM Results For 1.0g Si suspended dielectric used machining	159
B.7	$\mu$ -WEDM Results For 2g C suspended dielectric used machining	159

B.8	$\mu$ -WEDM Results For 2g Al suspended dielectric used machining	160
B.9	$\mu$ -WEDM Results For 2g Si suspended dielectric used machining	160
B.10	$\mu$ -WEDM Results For pure dielectric oil used machining	160
B.11	Datasets of normalized input and output values used in training for the modeling.	161

## LIST OF FIGURES

<u>Figure No.</u>		<u>Page No.</u>
1.1	Indicates concept about the micro-WEDM of gold coated Si in nano powder mixed dielectric oil.	5
1.2	The general structure of the ANN-GA model for the system	7
1.3	The flow chart of the complete research working procedures to fulfill the research objectives	8
2.1	Shows the experimental set-up of the p-Type Silicon wafer.	13
2.2	Represents rotor elastic force motor	14
2.3	Shows the process flow of axisymmetric hemispherical features fabrication.	16
2.4	Illustrates the EDM process of SiC using foil blade electrode.	17
2.5	(a) Demonstrates the EDM experimental set-up to texture multi-crystalline Silicon. (b) shows the comparison of textured and non-textured samples.	18
2.6	Shows the experimental set-up of die-sinking micro electro discharge machining of p-type silicon.	18
2.7	Represents the silicon electrodes with dimension of 250 $\mu\text{m}$ by 250 $\mu\text{m}$ and 5 mm height.	19
2.8	Shows schematic diagram of sliced Al deposited pure Germanium at right side and its SEM image at left side.	20
2.9	Shows SEM image of $\mu$ -actuator (left) and of $\mu$ -digital reflector produced at machining condition of 95 V and 1nF.	21
2.10	The MRR mechanism for the working fluid (a) without powder and (b) with powders during the normal discharge.	27
2.11	Schematic representation of mechanism of machining in NPMEDM	28
2.12	Shows the effect of pulse current along with nano powder concentration on MRR and TWR	29

3.1	The SEM images of three different nano powders.	40
3.2	Shows polished doped Si wafer	41
3.3	The images of polished doped and gold coated doped Si wafer	42
3.4	JFC Auto Fine Coater	42
3.5	DT -110 hybrid $\mu$ -EDM machine.	44
3.6	(a) & (b) show the actual $\mu$ -WEDM setup and the concept of experimental mechanism, respectively.	44
3.7	(a)The $\mu$ -WEDM set up for without powder experiments and (b) the HR-202 digital scaling machine.	46
3.8	Branson 3510 Ultrasonic cleaner.	47
3.9	Shows the surface of experimented Si wafer by WEDM after gold coating and etching.	48
3.10	The EDX analysis of Al powder mixed dielectric oil used machined slots at 85 V and 0.1nF for 10 min Au coated Si.	49
3.11	Shows the FESEM Machine for observing the surface topography of the Au coated Si wafers after machining (JEOL JSM-5600).	51
3.12	The Alicona infinite focus machine for 3D surface measurement.	52
3.13	(a) The measurement of ASR by Alicona and (b) the overall 3D topography of machined slot.	52
3.14	Optical Olympus Infinite focus machine.	53
3.15	(a) The schematic and (b) real figure of the calculation for each volume by Olympus infinite focus machine.	54
3.16	(a) shows the JEOL JSM 5600 Scanning electron Microscope machine and (b) shows the Liquid Nitrogen container for EDS analysis.	55
3.17	The schematic diagram of ANN.	57
3.18	The general topology of MLP neural network architecture.	59
3.19	The schematic flow chart of GA for optimal selection of machining conditions.	61

4.1	The graph of MRR at 80 V, 13 pF (a) for 160nm and (b) for 320nm gold coating.	65
4.2	The graph of SG analysis at 80 V and 13 pF for 160nm and 320nm gold coating.	68
4.3	The graph of ASR analysis at 80 V and 13 pF for 160nm and 320nm gold coating.	71
4.4	(a-d) represent the 3D Surface topography of machined slots of 320nm Au coated Si at 80V,13pF for 1g/L Al, C, Si and no powder mixed dielectric oil.	72
4.5	(a-c) represent the variation of 3D Surface topography of 160nm Au coated Si and (d-f) represent the 3D Surface topography of 320nm Au coated Si machined slots at 80V,13pF for three different concentrations of Si powder mixed dielectric oil machining.	72
4.6	Study of the Unevenness factor of the machined slots by NPM $\mu$ -WEDM process for C, Al and Si nano powder and without powder machining at 80V, 13pF.	74
4.7	Study of the rate of the short circuit occurrences of the machined slots by NPM $\mu$ -WEDM process for C, Al and Si nano powder and without powder machining at 80V, 13pF.	76
4.8	(a-f) represent the MRR at 85 V with different capacitances for 160nm and 320nm gold coating Si.	78
4.9	(a-f) represent the MRR at 100 V with different capacitances for 160nm and 320nm gold coating Si.	80
4.10	(a-f) represent the SG at 85 V with different capacitances for 160nm and 320nm gold coating Si.	84
4.11	(a-f) represent the SR at 85 V with different capacitances for 160nm and 320nm gold coating.	87
4.12	Study of the Unevenness factor of the machined slots for C, Al and Si nano powder and without powder machining at 85V, with 0.1nF, 10nF and 400nF for 160nm and 320nm Au coating at three different powder concentrations.	91
4.13	Study of the short circuit occurrences rate for C, Al and Si nano powder and without powder machining at 85V with 0.1nF for 160nm and 320nm Au coated machined slots in 0.2g/L powder concentration.	92
5.1	The images of artificial neuron cell.	95

5.2	The image of the general structure of a 4-n-1-1 MLP network model.	97
5.3	The process of updating the weights of a MLP network model.	98
5.4	The process of training the model using LMBP algorithm.	102
5.5	Variation of MSE and $R^2$ at different number of hidden neurons.	106
5.6	Variation of MSE and $R^2$ with different number of network model configuration.	106
5.7	(a) shows the regression analysis values for the model and (b) shows the training performance of the model.	107
5.8	Comparison of Experimental and ANN output for SG of C for modelling dataset	108
5.9	Comparison of experimental and ANN output for SG of C for the validation data set	110
5.10	Shows pair of input parameters impact on the spark gap.	111
5.11	Variation of MSE and $R^2$ at different number of hidden neurons.	112
5.12	Variation of MSE and $R^2$ with different number of network model configuration.	113
5.13	(a) shows the regression analysis values for the model and (b) shows the training performance of the model.	113
5.14	Comparison of Experimental and ANN output for MRR of Al for modeling dataset.	114
5.15	Comparison of experimental and ANN output for MRR of Al for the validation data sets.	115
5.16	Influence of input parameters on material removal rate.	117
5.17	Variation of MSE and $R^2$ at different number of hidden neurons.	118
5.18	Variation of MSE and $R^2$ with different number of network model configuration.	118
5.19	(a) shows the regression analysis values for the model and (b) shows the training performance of the model	119



5.20	Comparison of Experimental and ANN output for ASR of Al for modeling dataset	119
5.21	Comparison of experimental and ANN output for ASR of Al for the validation data set.	121
5.22	Influence of input parameters on average surface roughness.	122
5.23	The flow chart of the general structure of a GA optimization.	123
5.24	The best and mean value of the fitness function and the values of the corresponding input variables for SG of C.	128
5.25	The best and mean value of the fitness function and the values of the corresponding input variables.	130
5.26	The best and mean value of the fitness function and the values of the corresponding input variables for ASR of Al.	131
C.1	(a-h) represent the Surface topography of machined slots of 160nm and 320nm Au coated Si at 80 V, 13pF with 2g/L C, Al, Si and no powder mixed EDM oil.	163
C.2	(a-h) represent the Surface topography of 320nm Au coated Si at two different energies with 0.2g/L C, Al, Si and no powder mixed dielectric oil.	163
C.3	(a-h) represent the Surface topography of 160nm Au coated Si at two different energies with 0.2g/L C, Al, Si and no powder mixed dielectric oil.	164
C.4	(a-h) represent the Surface topography of 160nm Au coated machined Si at 85 V and 100V with 0.1nF for 0.2g/L C, Al, Si and no powder mixed dielectric oil.	164
C.5	(a-h) represent the FESEM images of 1g/L and 2g/L Al, C, Si and no powder used machining of 320nm Au coated Si at 80 V and 13pF.	165
C.6	(a-d) represent the FESEM images of 2g/L Al, C, Si and no powder used machining of 320nm Au coated Si at 100 V and 10nF.	165
C.7	(a-d) represent the FESEM images for 160nm and (e-h) for 320nm Au coated Si at 0.2g/L C used machining at different discharge energies.	166
C.8	(a-f) represent the MRR at 115 V with different capacitances for 160nm and 320nm gold coating Si.	166

C.9	(a-f) represent the SG at 85 V with different capacitances for 160nm and 320nm gold coating Si.	167
C.10	(a-f) represent the SG at 85 V with different capacitances for 160nm and 320nm gold coating Si.	167
C.11	(a-f) represent the SR at 85 V with different capacitances for 160nm and 320nm gold coating Si.	168
C.12	(a-f) represent the SR at 85 V with different capacitances for 160nm and 320nm gold coating Si.	168
C.13	Study of the Unevenness factor of the machined slots for 0.2 g/L C, Al and Si powder and without powder machining at 100V, with 0.1nF, 10nF and 400nF.	169
C.14	Study of the Unevenness factor of the machined slots by for 0.2 g/L C, Al and Si powder and without powder machining at 115V, with 0.1nF, 10nF and 400nF.	169

## LIST OF SYMBOLS

Al	Aluminum
Au	Gold
Ar	Argon
Al <sub>2</sub> O <sub>3</sub>	Aluminum oxide
C	Carbon
Cr	Chromium
C	Capacitance
Cu	Copper
E	Energy
F	Farad
Ge	Germanium
g/cm <sup>3</sup>	Gram per centimeter cube
g/mL	Gram per millileter
g/L	Gram per Liter
I <sub>p</sub>	Pulse current
min	Minute
μm	Micro-meter
μJ	Micro Joule
μF	Micro-Farad
mm	Millimeter
MoS <sub>2</sub>	Molybdenum disulfide
mA	Milliampere

mm <sup>3</sup> /min	Millimeter cube per minute
mm/s	Millimeter per second
N	Newton
nF	Nano-Farad
nm	Nano-meter
nJ	Nano joule
nos/min	Number of short circuit per minute
Pa	Pascal
pF	Pico-Farad
R <sub>a</sub>	Average surface roughness
R <sub>max</sub>	Maximum surface roughness
Si	Silicon
SiC	Silicon Carbide
T <sub>on</sub>	Pulse on time
T <sub>off</sub>	Pulse off time
Ti	Titanium
TiC	Titanium Carbide
V	Voltage
+ve	Positive charge
-ve	Negative charge
Ω-cm	Ohm centimeter
"	Inches

## LIST OF ABBREVIATIONS

ABC	Artificial bee colony
AJM	Abrasive Jet Machining
ASR	Average Surface roughness
ANN	Artificial Neural Network
ANN-GA	Artificial neural network-Genetic algorithm
BPN/BPNN	Back propagation neural network
CNC	Computer numerical control
CT	Coating Thickness
CNT	Carbon nano tube
EDS	Electro discharge Spectroscopy
EDM	Electro discharge machining
EDX	Electro energy dispersive x-ray analysis
ECM	Electro-chemical Machining
EWR	Electrode wear rate
FESEM	Field Emission Scanning Electron Microscope
GA	Genetic Algorithm
i.e	(id est) that is
LMBP	Levenberg-Marquardt Back propagation algorithm
MEMS	Micro electro mechanical system
$\mu$ -EDM	Micro-electro discharge machining
$\mu$ -WEDM	Micro-wire electro discharge machining
$\mu$ -WEDG	Micro wire electro discharge grinding

MRR	Material removal rate
MSE	Mean square error
MLP	Multi-layer perceptron
NP	No powder
NPM	Nano powder mixed
NPMEDM	Nano powder mixed EDM
NPM $\mu$ -WEDM	Nano powder mixed $\mu$ -WEDM
PC	Powder concentration
PMEDM	Powder mixed EDM
RSM	Response surface methodology
RBFN	Radial basis function neural network
$R^2$	Correlation coefficient
SEM	Scanning Electron Microscopy
SR	Surface Roughness
SG	Spark Gap
SD	Standard Deviation
TWR	Tool wear ratio
USM	Ultrasonic Machining
WEDM	Wire electro discharge machining

# CHAPTER ONE

## INTRODUCTION

### 1.1 BACKGROUND

In recent years, electrical discharge machining (EDM) and micro wire electrical discharge machining ( $\mu$ -WEDM) have been considered as a potential machining technique to meet various industrial and diverse engineering requirements due to their excellent characteristics and advantages. The material eroding process of EDM and Micro WEDM are identical, however, their functional characteristics differ from each other. The  $\mu$ -WEDM process is a well-established special type variant of conventional EDM process. In the  $\mu$ -WEDM process, electrical discharges are generated between a flexible metallic wire and work-piece material to erode materials from the work-piece without causing direct contact between them (Ho, Newman, Rahimifard, & Allen, 2004).

This WEDM process is widely used to machine electrically conductive and semi-conductive materials like Silicon(Si), Germanium (Ge) owing to its physical nature and feasibilities. The Silicon is the most common engineering material in MEMS-based fabrication and electronic industry. Having excellent physical properties, polished silicon mirrors has large demands in sensors and optical industries as well. Takino et al. first introduced WEDM technology (Takino et al., 2004, 2005) which could be an effective way for various contours to fabricate the complex 2D or 3D shaped Silicon mirrors. However, Silicon has some physical properties like high surface resistance than bulk body resistance which makes it difficult to machine by the  $\mu$ -WEDM process.

Therefore, machining of Silicon like materials is becoming very challenging and no more extensive works have been carried out in this prospect.

To overcome such challenges to machine Si like materials, many works have been carried out with different techniques to achieve the finest surface finish of Silicon work-piece with better machining stability. Reynaerts et al. (Reynaerts & Van Brussel, 1997) proposed the conductive polishing on the p-type Silicon as positive and electrode as negative and vice versa for n-type material in EDM operation to enhance the machining stability and accuracy. Song et al. (Song, Meeusen, Reynaerts, & Van Brussel, 2000) studied the consequences of  $\mu$ -EDM on highly doped p-type Si wafer. Recently, Saleh et al. (Saleh, Rasheed, & Muthalif, 2015) experimented the influences of temporary Gold (Au) coating on Silicon wafer for micro-EDM and micro-WEDM treatment. It was found that at a very low discharge energy ( $\sim <451.25$  nJ), the micro-WEDM of pure silicon was impossible without gold coating. Further, the machining stability by this temporary gold coating process was significantly improved.

The powder mixed EDM/WEDM is another approach to signify the machining stability and accuracy. In the last era, powder mixed EDM has drawn a lot of attention to the researchers because of its proficiencies to enhance process capabilities over traditional machining process (Kansal, Singh, & Kumar, 2007). It was found that powder assisted dielectric affects the spark gap along with the discharging process which influences the performance of the machining process significantly.

In recent years, Tan et al. (Tan, Yeo, & Tan, 2008) examined the effect of nano powder assisted machining by micro-EDM and found an improvement in the machined surface. In addition, Jahan et al. (M. Jahan, Anwar, Wong, & Rahman, 2009; M. P. Jahan, Rahman, & San Wong, 2011) showed that by using different concentrations of graphite nano powder mixed dielectric oil it could be possible to get surface roughness